Supplemental Information

All-Dry-Processed Zn-Based Inorganic–Organic Hybrid Photoresists for EUV Lithography

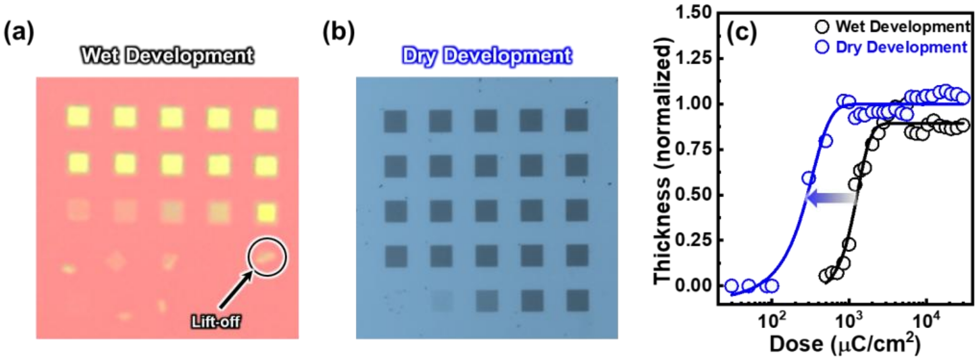


Figure 1. Optical images of the dose matrix for Zn-based resist using **(a)** Wet development, and **(b)** Dry development. **(c)** Comparison of the corresponding contrast curves.

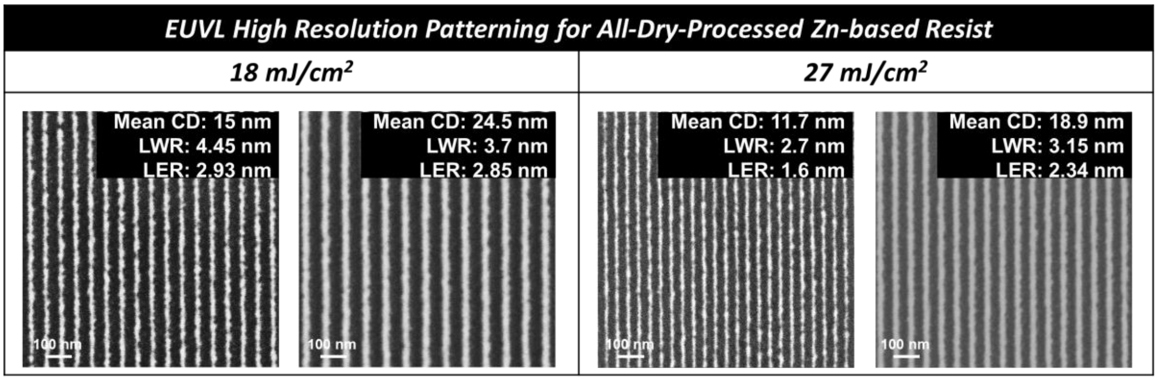
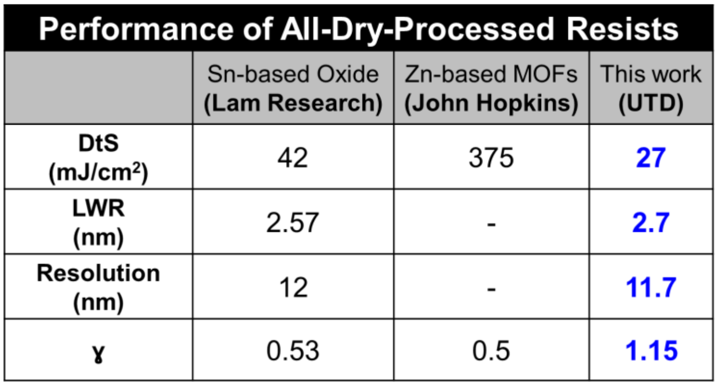


Figure 2. EUVL High Resolution Patterning for All-Dry-Processed Zn-based Resist.



Performance of All-Dry-Processed Resists

	Sn-based Oxide **(Lam Research)**	Zn-based MOFs **(John Hopkins)**	This work **(UTD)**
DtS (mJ/cm^2)	42	375	**27**
LWR (nm)	2.57	-	**2.7**
Resolution (nm)	12	-	**11.7**
γ	0.53	0.5	**1.15**

Table 1. Comparative performance evaluation of current all-dry-processed resists.